

D1 wherein said semiconductor layer has substantially no grain boundaries.

D2 10. (Amended) A semiconductor device comprising:
a substrate having an insulating surface;
at least one thin film transistor formed on said insulating surface, said thin film transistor having a semiconductor layer comprising source, drain and channel regions;
an insulating film comprising an inorganic material formed on said thin film transistor;
an organic resin film provided over said insulating film; and
a pixel electrode formed over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film,
wherein said semiconductor layer exhibits a peak of Raman spectra, displaced from 522 cm^{-1} to the lower frequency direction, and
wherein said semiconductor layer has substantially no grain boundaries.

D3 19. (Amended) A semiconductor device comprising:
a substrate having an insulating surface;
at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:
a semiconductor layer having source, drain and channel regions;
a gate insulating layer adjacent to said channel region; and
a gate electrode adjacent to said channel region;
an insulating film comprising an inorganic material formed on said thin film transistor; and
an organic resin film provided over said insulating film;
wherein said semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction,
wherein said semiconductor layer has substantially no grain boundaries.

D4 32. (Amended) A semiconductor device comprising:

a substrate having an insulating surface;
at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

D4
a semiconductor layer having source, drain and channel regions;
a gate insulating layer adjacent to said channel region;
an insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said thin film transistor and said insulating film;

wherein said semiconductor layer comprises silicon and exhibits a peak of Raman spectra, displaced from 522 cm^{-1} to the lower frequency direction, and
wherein said semiconductor layer has substantially no grain boundaries.

45. (Amended) A semiconductor device comprising:

D5
a substrate having an insulating surface;
at least an n-channel thin film transistor and at least a p-channel thin film transistor both formed over said substrate, each of said n-channel and p-channel thin film transistors comprising:

a semiconductor layer having source, drain and channel regions;
a gate insulating layer adjacent to said channel region; and
a gate electrode adjacent to said channel region;
an insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said insulating film;
wherein said semiconductor layer exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction, and
wherein said semiconductor layer has substantially no grain boundaries.

68. (Amended) A semiconductor device comprising:

D6
a substrate having an insulating surface;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

a semiconductor layer having source, drain and channel regions;

an insulating film comprising an inorganic material formed on said thin film

transistor;

an organic resin film provided over said insulating film; and

a pixel electrode provided over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film;

wherein said semiconductor layer exhibits a peak of Raman spectra, displaced from 522 cm^{-1} to the lower frequency direction, and

wherein said semiconductor layer has substantially no grain boundaries.
